

SHINDENGEN

VX-2 Series Power MOSFET

N-Channel Enhancement type

**2SK2178
(F2E50VX2)**

500V 2A

FEATURES

Input capacitance (C_{iss}) is small.
Especially, input capacitance at 0 bias is small.
The static $R_{ds(on)}$ is small.
The switching time is fast.

APPLICATION

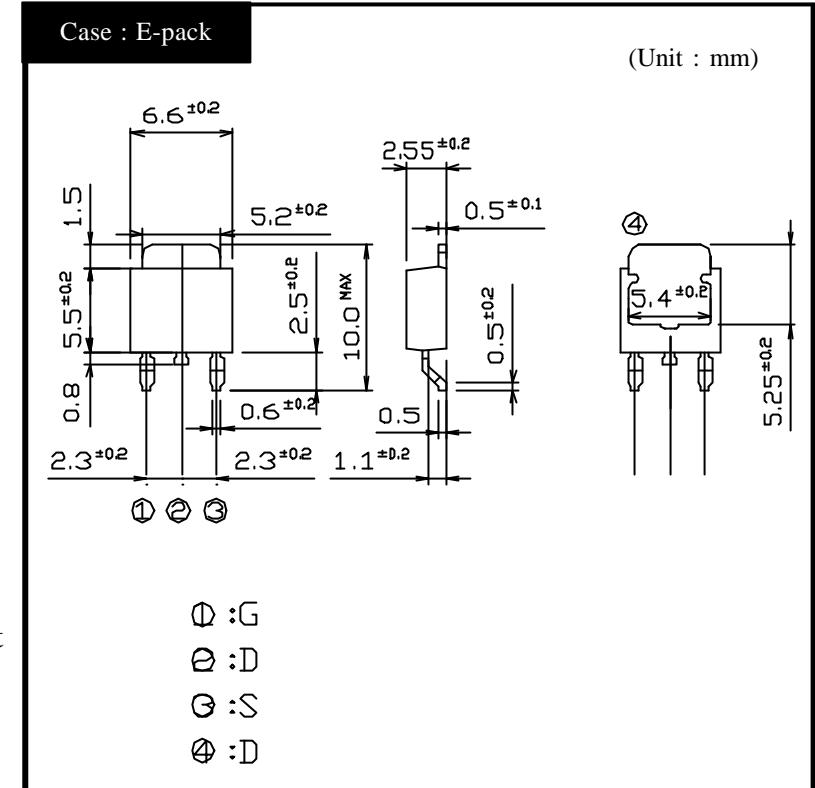
Switching power supply of AC 100V input
High voltage power supply
Inverter

RATINGS

Absolute Maximum Ratings ($T_c = 25^\circ C$)

Item	Symbol	Conditions	Ratings	Unit
Storage Temperature	T_{stg}		-55 ~ 150	
Channel Temperature	T_{ch}		150	
Drain-Source Voltage	V_{DSS}		500	V
Gate-Source Voltage	V_{GSS}		± 30	
Continuous Drain Current (DC)	I_D		2	
Continuous Drain Current (Peak)	I_{DP}		6	
Continuous Source Current (DC)	I_S		2	
Total Power Dissipation	P_T		15	W
Single Pulse Avalanche Current	I_{AS}	$T_{ch} = 25^\circ C$	2	A

OUTLINE DIMENSIONS



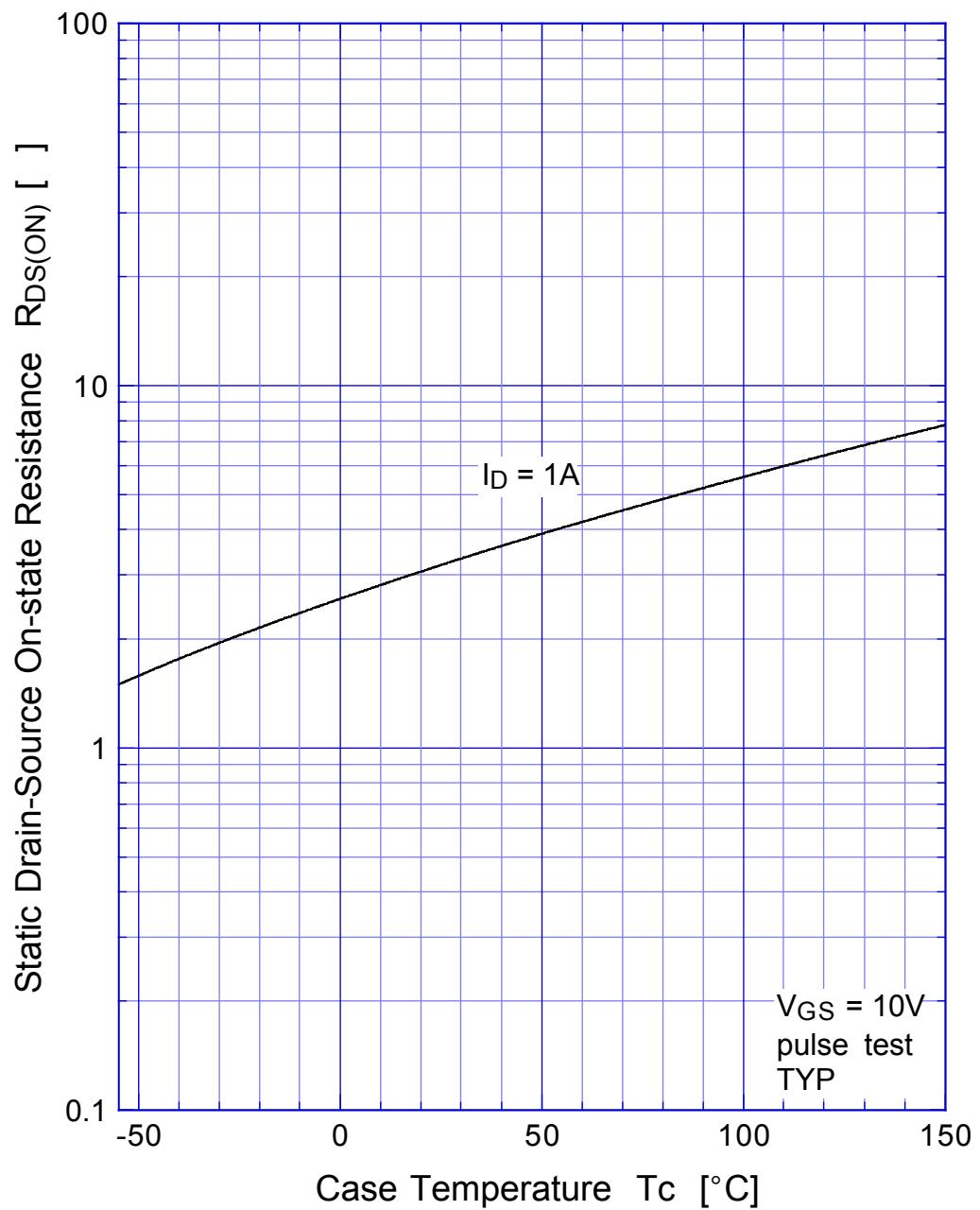
VX-2 Series Power MOSFET

2SK2178 (F2E50VX2)

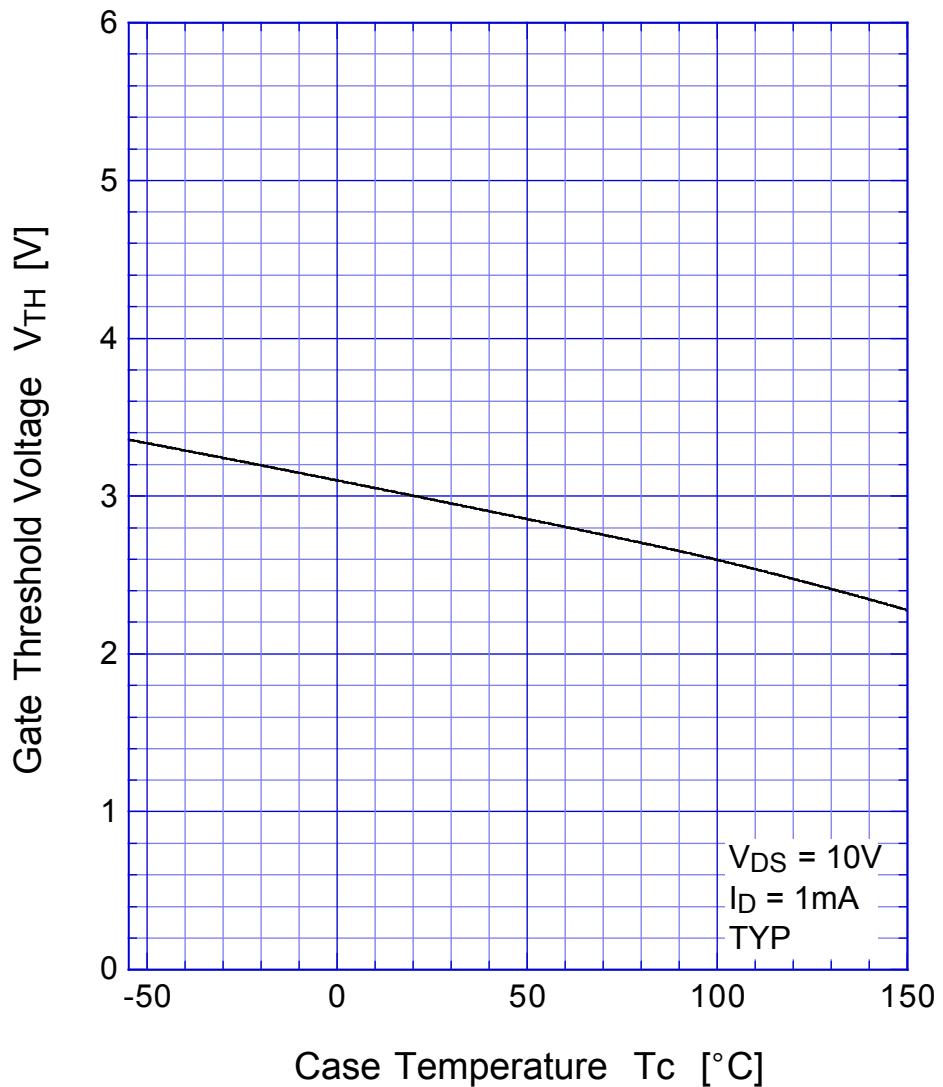
●Electrical Characteristics T_c = 25°C

Item	Symbol	Conditions	Min.	Typ.	Max.	Unit
Drain-Source Breakdown Voltage	V _{(BR)DSS}	ID = 1mA, VGS = 0V	500			V
Zero Gate Voltage Drain Current	I _{DSS}	VDS = 500V, VGS = 0V			250	μA
Gate-Source Leakage Current	I _{GSS}	VGS = ±30V, VDS = 0V			±0.1	
Forward Transconductance	g _{fS}	ID = 1A, VDS = 10V	0.6	1.3		S
Static Drain-Source On-state Resistance	R _{D(S)ON}	ID = 1A, VGS = 10V		3.2	4.0	Ω
Gate Threshold Voltage	V _{TH}	ID = 0.3mA, VDS = 10V	2.5	3.0	3.5	V
Source-Drain Diode Forwade Voltage	V _{SD}	IS = 1A, VGS = 0V			1.5	
Thermal Resistance	θ _{jc}	junction to case			8.33	°C/W
Total Gate Charge	Q _g	VDD = 400V, VGS = 10V, ID = 2A		9		nC
Input Capacitance	C _{iss}	VDS = 10V, VGS = 0V, f = 1MHz	220			pF
Reverse Transfer Capacitance	C _{rss}			17		
Output Capacitance	C _{oss}			55		
Turn-On Time	t _{on}	ID = 1A, VGS = 10V, RL = 150Ω	40	75	ns	
Turn-Off Time	t _{off}			70	120	

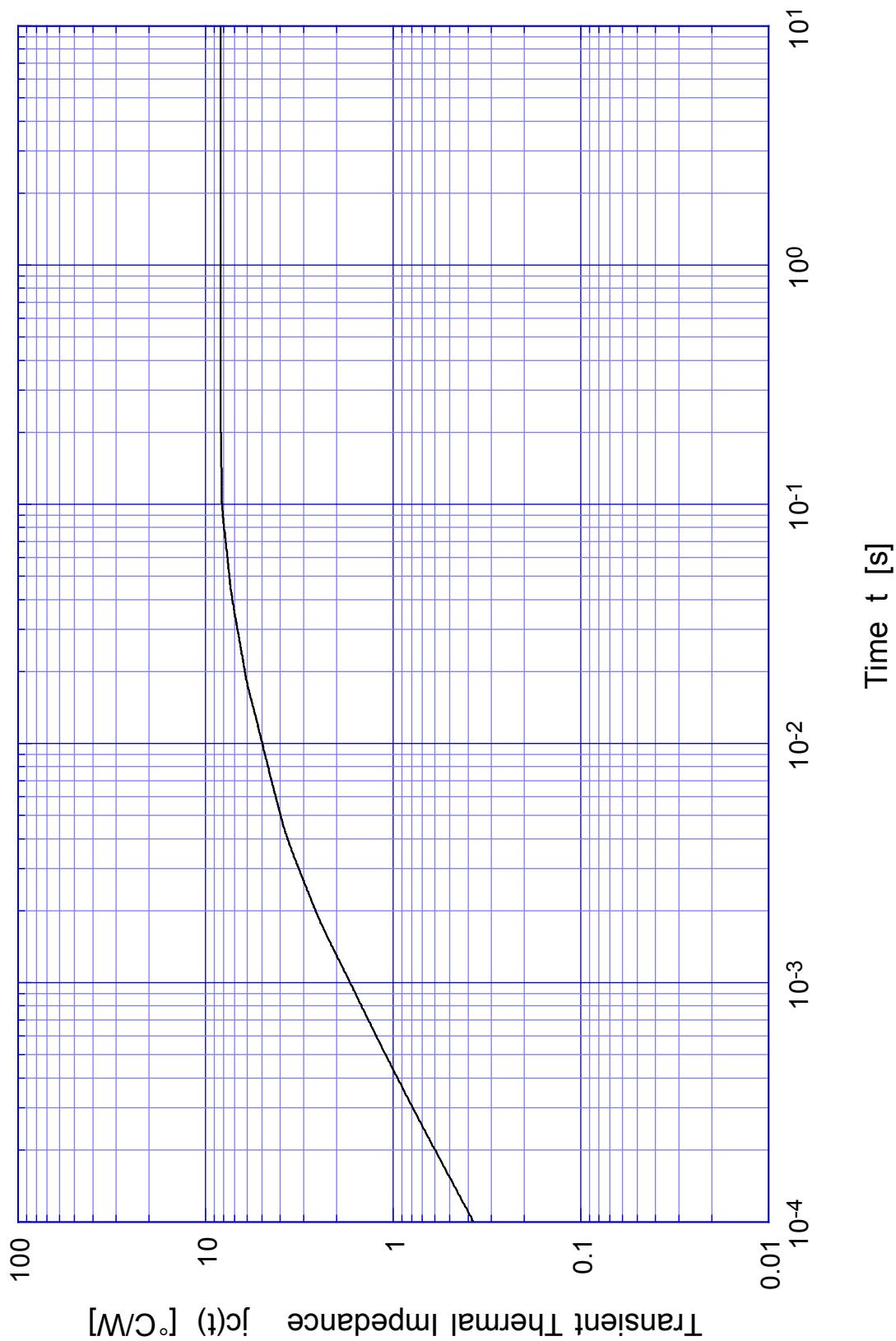
2SK2178 Static Drain-Source On-state Resistance



2SK2178 Gate Threshold Voltage



2SK2178 Transient Thermal Impedance



2SK2178

Power Derating

